



60V +175°C P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} max	I _D max T _C = +25°C		
-60V	$50m\Omega$ @ $V_{GS} = -10V$	-23.6A		
	$70m\Omega$ @ $V_{GS} = -4.5V$	-20A		

Features

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching Ensures More Reliable and Robust End Application
- Low Q_q Minimizes Switching Loss
- Low R_{DS(ON)} Minimizes On State Loss
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Engine Management Systems
- Body Control Electronics
- DC-DC Converters

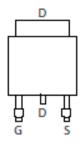
Mechanical Data

- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound;
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208[®]
- Weight: 0.315 grams (Approximate)

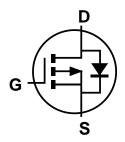








Pin Out Top View



Equivalent Circuit

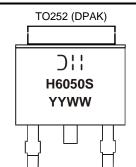
Ordering Information (Note 5)

Part Number	Case	Packaging
DMPH6050SK3Q-13	TO252 (DPAK)	2,500/Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/product_compliance_definitions.html.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



Dill = Manufacturer's Marking
H6050S = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 15 = 2015)
WW = Week Code (01 to 53)



Maximum Ratings ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Units		
Drain-Source Voltage	V_{DSS}	-60	V		
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Dusin Comment (Note 7) \	Steady State	$T_C = +25$ °C $T_C = +70$ °C	I _D	-23.6 -19	А
Continuous Drain Current (Note 7) V _{GS} = -10V	Steady State	$T_A = +25$ °C $T_A = +70$ °C	I _D	-7.2 -6.0	А
Pulsed Drain Current (10µs pulse, duty cycle = 1%)	I _{DM}	-40	Α		
Maximum Continuous Body Diode Forward Current (Note 7)			Is	-3.8	Α
Avalanche Current (Note 8) L = 0.1mH			I _{AS}	-25	Α
Avalanche Energy (Note 8) L = 0.1mH			E _{AS}	31	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units	
Total Power Dissipation (Note 6)		P_{D}	1.9	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{ hetaJA}$	80	°C/W
Total Power Dissipation (Note 7)		P _D	3.8	W
Thermal Resistance, Junction to Ambient (Note 7) Steady State		$R_{ hetaJA}$	39	°C/W
Thermal Resistance, Junction to Case (Note 7)		$R_{ heta JC}$	3	
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage	BV _{DSS}	-60	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	_	_	-1	μΑ	$V_{DS} = -60V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	V _{GS(TH)}	-1	_	-3	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
Static Drain-Source On-Resistance		_	_	50	mΩ	$V_{GS} = -10V, I_D = -7A$	
Static Dialit-Source Off-Resistance	R _{DS(ON)}	_	_	70	mΩ	$V_{GS} = -4.5V$, $I_{D} = -7A$	
Diode Forward Voltage	V_{SD}	_	-0.7	-1.2	V	$V_{GS} = 0V, I_{S} = -1A$	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	C _{iss}		1,377	_	pF		
Output Capacitance	Coss	_	87	-	рF	$V_{DS} = -30V, V_{GS} = 0V,$ - f = 1MHz	
Reverse Transfer Capacitance	Crss	_	68	l	рF	1 – 11011 12	
Gate Resistance	R_g	_	12	l	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = -4.5V)	Q_g	_	12	-	nC		
Total Gate Charge (V _{GS} = -10V)	Q_g	_	25	l	nC	V _{DS} = -30V. In = -5A	
Gate-Source Charge	Q_{gs}	_	3.8	-	nC	VDS = -30V, ID = -5A	
Gate-Drain Charge	Q_{gd}	_	4.9	_	nC		
Turn-On Delay Time	t _{D(ON)}	_	5.3	_	ns		
Turn-On Rise Time	t _R	_	8.6	_	ns	$V_{DS} = -30V, V_{GS} = -10V,$	
Turn-Off Delay Time	t _{D(OFF)}	_	49.4	_	ns	$R_G = 3\Omega$, $I_D = -5A$	
Turn-Off Fall Time	t _F		29.7	_	ns		
Body Diode Reverse Recovery Time	t _{RR}	_	14.2	_	ns	L 5A di/dt 400A/c-	
Body Diode Reverse Recovery Charge	Q _{RR}		7.9	_	nC	$I_F = -5A$, di/dt = 100A/ μ s	

6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout. 7. Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate. Notes:

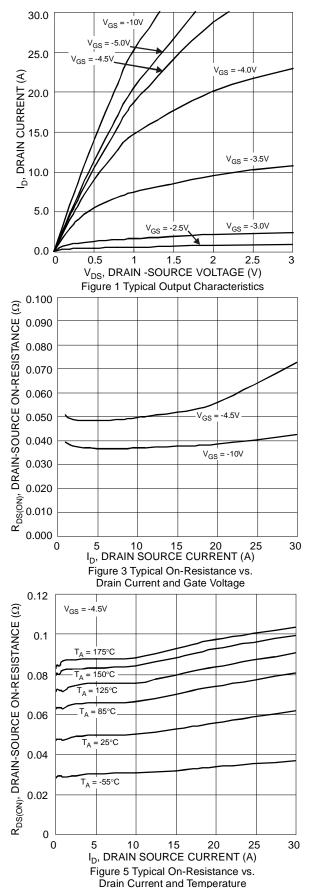
^{8.} I_{AS} and E_{AS} rating are based on low frequency and duty cycles to keep $T_J = +25^{\circ}C$.

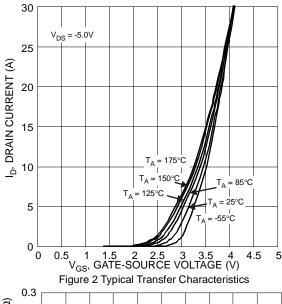
^{9.} Short duration pulse test used to minimize self-heating effect.

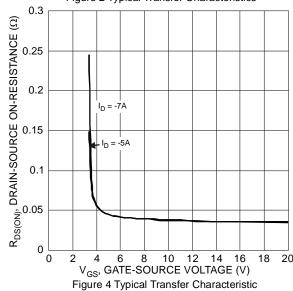
10. Guaranteed by design. Not subject to product testing.











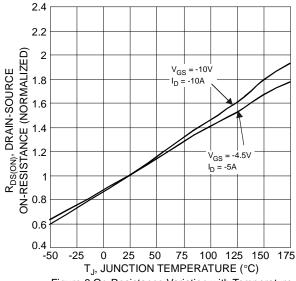
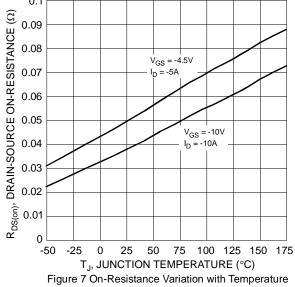
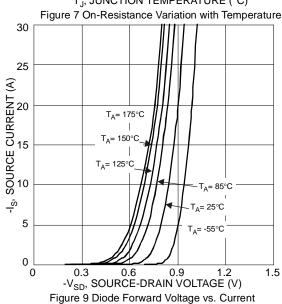
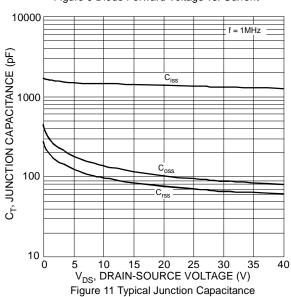


Figure 6 On-Resistance Variation with Temperature









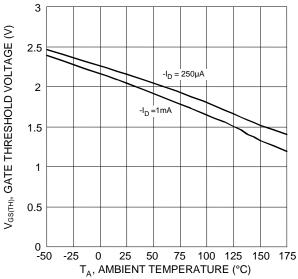


Figure 8 Gate Threshold Variation vs. Ambient Temperature

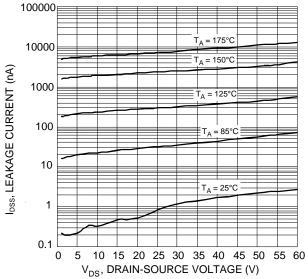


Figure 10 Typical Drain-Source Leakage Current vs. Voltage

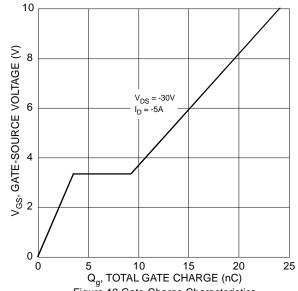


Figure 12 Gate-Charge Characteristics



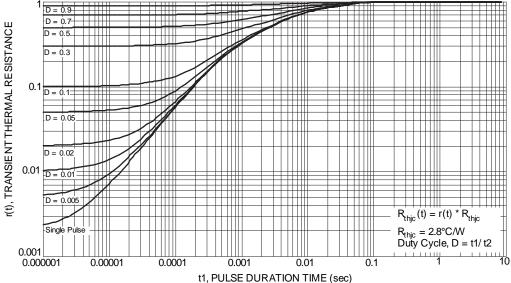
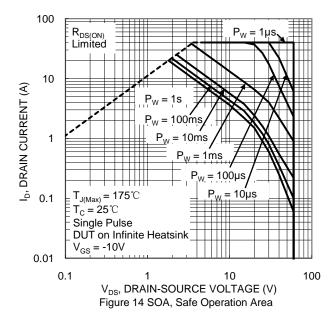


Figure 13 Transient Thermal Resistance

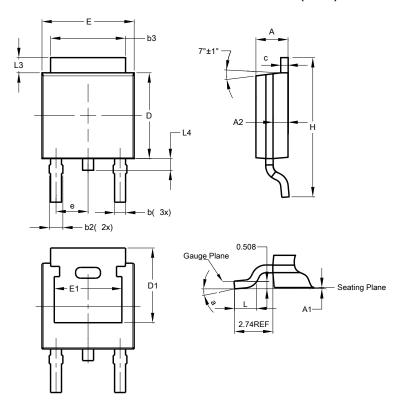




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO252 (DPAK)

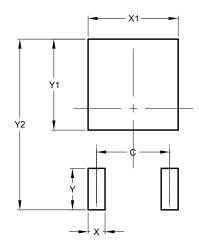


TO252 (DPAK)					
Dim	Min	Max	Тур		
Α	2.19	2.39	2.29		
A 1	0.00	0.13	0.08		
A2	0.97	1.17	1.07		
q	0.64	0.88	0.783		
b2	0.76	1.14	0.95		
b3	5.21	5.46	5.33		
С	0.45	0.58	0.531		
D	6.00	6.20	6.10		
D1	5.21	-	-		
е	-	-	2.286		
Е	6.45	6.70	6.58		
E1	4.32	-	-		
Н	9.40	10.41	9.91		
Г	1.40	1.78	1.59		
L3	0.88	1.27	1.08		
L4	0.64	1.02	0.83		
а	0°	10°	-		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO252 (DPAK)



Dimensions	Value (in mm)		
С	4.572		
Х	1.060		
X1	5.632		
Υ	2.600		
Y1	5.700		
Y2	10.700		



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